

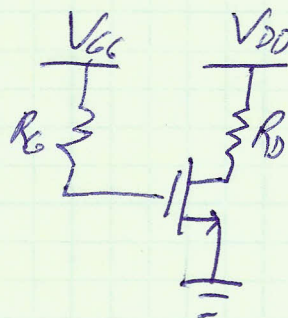
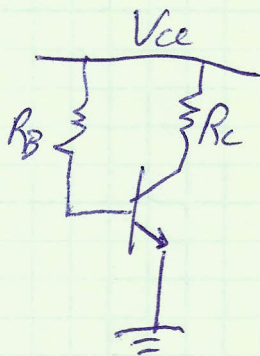
- Capacitive Coupling
 - Fixed bias
 - Emitter degeneration bias with voltage divider
 - Self bias
 - Similar bias circuits for MOSFETs
 - Current Mirrors
 - Diode small signal model
 - MOSFET small signal model
 - BJT small signal model
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Capacitive coupling

- DC signals (bias) see capacitors as open circuit
- AC signals see capacitors as short circuit
assuming capacitor is large enough, frequency is high enough
- Used to separate AC signal from DC bias

Fixed bias

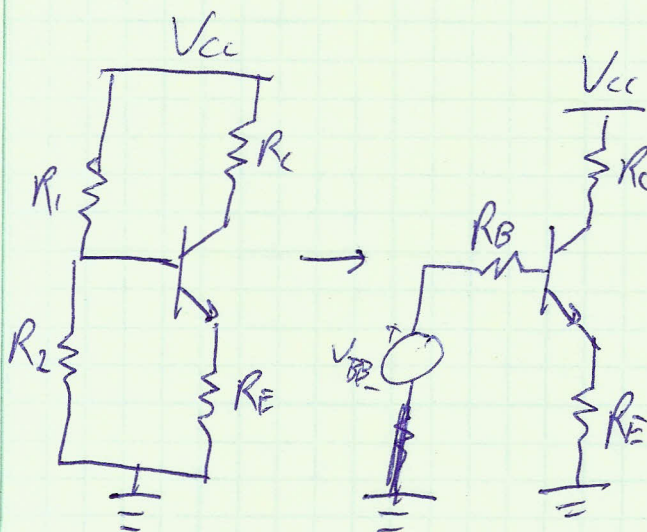
- Simple bias circuit, but not stable
- Q point can vary with β , V_T , and temperature



need 2 voltage sources for MOSFET

Emitter degeneration with voltage divider

- Q point is independent of β and V_{be} variations
thus independent of temperature and device variations



Conditions for stability

$$R_B \ll (1 + \beta) R_E$$

$$V_E > 1V$$

$\gg$ means $\sim 10\times$

Self bias

- Stable bias circuit, independent of β and V_{be}
- Uses R_c as feedback resistor

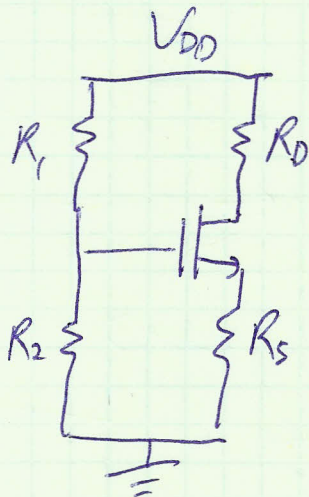


Stability condition

$$R_B \ll (\beta - 1) R_c$$

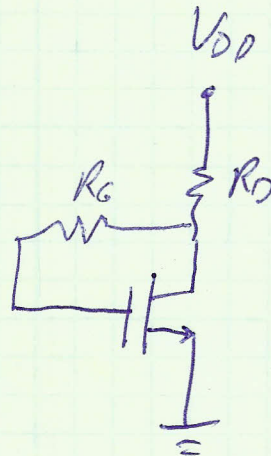
MOSFET bias circuits

Source degeneration:



R_1, R_2 can
be large
(M2)

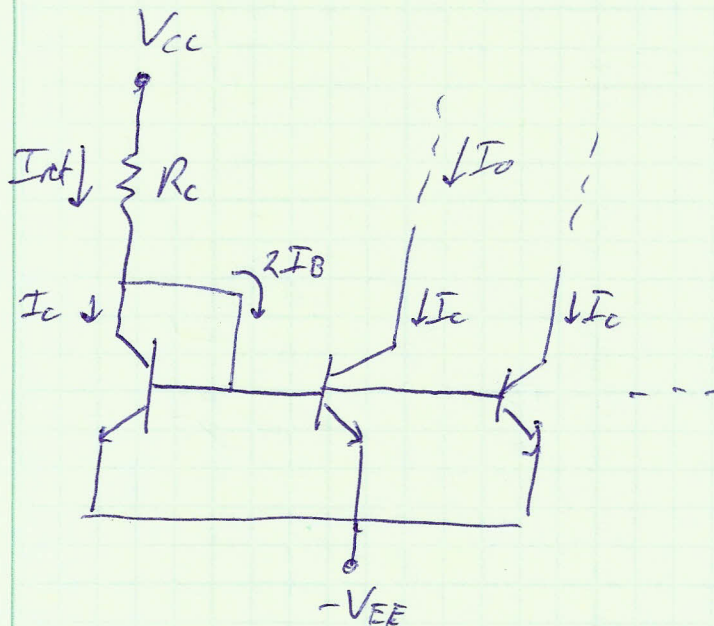
Self bias:



R_G only needed
for amplifier use,
otherwise input
connected to output

These are not as stable as BJT bias circuits because of quadratic I_D - V_{GS} relationship, but relatively stable

Current Mirrors



for single current mirror

$$\frac{I_o}{I_{ref}} = \frac{\beta}{\beta + 2}$$

I_o can be multiplied by using multiple transistors at output

- MOSFET current mirror is similar but we can scale W/L instead of using multiple transistors

Diode Small Signal Model

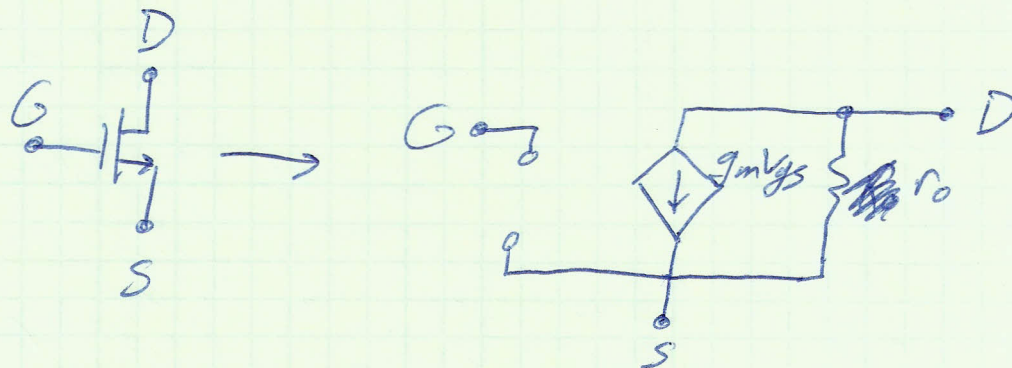
In on state:

$$\text{Diode} \rightarrow \text{resistor } r_d = \frac{nV_T}{I_D}$$

I_D is DC bias current

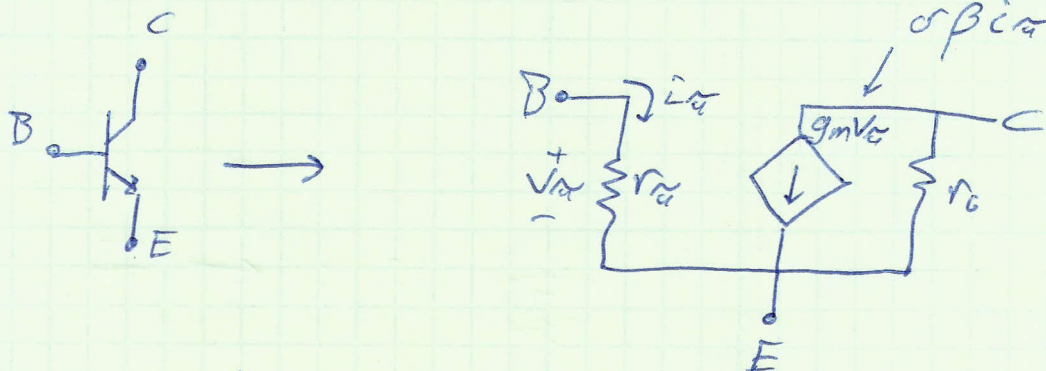
$n=2$ for discrete silicon diodes

$V_T = 25\text{mV}$ at 300K

MOSFET small signal model

$$g_m = \frac{2I_D}{V_{GS} - V_T} \quad \text{or} \quad \frac{2I_D}{V_{SG} - |V_T|}$$

$$r_o = \frac{V_A + V_{DS}}{I_D} \approx \frac{V_A}{I_D}$$

BJT small signal model

$$r_{\pi} = \frac{n V_T}{I_B}$$

$$g_m = \frac{I_C}{n V_T}$$

$$g_m r_{\pi} = \beta$$

$$r_o = \frac{V_A + V_{CE}}{I_C} \approx \frac{V_A}{I_C}$$